Technical Data Data Sheet 3305, Rev. A

## 125NQ015/R-1 SCHOTTKY RECTIFIER

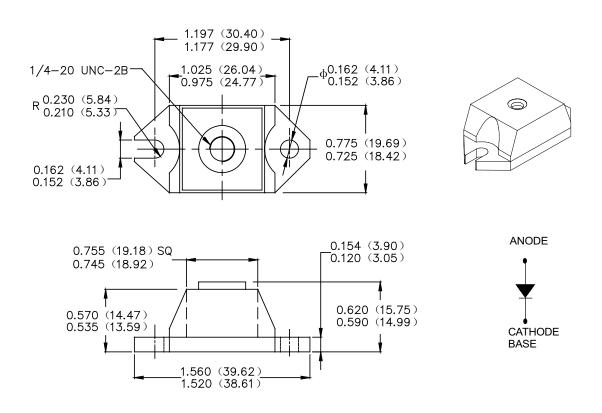
### **Applications:**

• Switching power supply • Free-Wheeling diodes • Reverse battery protection • Converters

### Features:

- 125 °C T<sub>J</sub> operation
- Unique high power, Half-Pak module
- Optimized for OR-ing application
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Ultra low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability

### Mechanical Dimensions: In Inches / mm



PRM1-1(HALF PAK Module)



# Data Sheet 3305, Rev. A Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	15(DC)	V
			25(Working)	
Max. Average Forward	I <sub>F(AV)</sub>	50% duty cycle @T <sub>C</sub> = 71 °C,	120	Α
Current	. ,	rectangular wave form		
Max. Peak One Cycle Non-				
Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	2040	Α
Non-Repetitive Avalanche	E <sub>AS</sub>	$T_J = 25 ^{\circ}\text{C}$ , $I_{AS} = 2 \text{Amps}$ ,	9	mJ
Energy		L = 4.5 mH		
		Current decaying linearly to		
Repetitive Avalanche	I <sub>AR</sub>	zero in 1 µsec Frequency	2	Α
Current		limited by T₁ max. V₄ = 1.5 x		
		V <sub>R</sub> typical		

### **Electrical Characteristics:**

Characteristics	<b>Symbol</b>	Condition	Max.	Units
Max. Forward Voltage Drop*	$V_{F1}$	@ 120 A, Pulse, T <sub>J</sub> = 25 °C	0.39	V
		@ 240 A, Pulse, T <sub>J</sub> = 25 °C	0.52	
	V	@ 120 A, Pulse, T <sub>J</sub> = 75 °C	0.33	V
	$V_{F2}$	@ 240 A, Pulse, T <sub>J</sub> = 75 °C	0.45	V
Max. Reverse Current *	I <sub>R1</sub>	$@V_R = \text{rated } V_R, T_J = 25  ^{\circ}\text{C}$	40	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R, T_J = 100  ^{\circ}\text{C}$	2000	mA
	I <sub>R3</sub>	$@V_R = 12 \text{ V}, T_J = 100 ^{\circ}\text{C}$	1780	mA
	I <sub>R4</sub>	$@V_R = 5 \text{ V}, T_J = 100 ^{\circ}\text{C}$	1080	mA
Max. Junction Capacitance	Ст	$@V_R = 5 \text{ V}, T_C = 25 ^{\circ}\text{C}$	7700	pF
		$f_{SIG} = 1MHz$		
Typical Series Inductance	L <sub>S</sub>	Measured lead to lead 5 mm	7.0	nΗ
		from package body		
Max. Voltage Rate of	dv/dt	-	10,000	V/μs
Change				

<sup>\*</sup> Pulse Width < 300µs, Duty Cycle <2%

# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification		Units	
Max. Junction Temperature	TJ	-	-55 to +125		°C	
Max. Storage Temperature	$T_{stg}$	-	-55 to +150		°C	
Maximum Thermal	$R_{\theta JC}$	DC operation	0.40		°C/W	
Resistance Junction to Case						
Maximum Thermal	$R_{\theta CS}$	Mounting surface,	0.15		°C/W	
Resistance, Case to Heat		smooth and greased				
Sink						
Approximate Weight	wt	-	25.6		g	
Mounting Torque	$T_M$	-	Mounting	23 (min)	Kg-cm	
			Torque	29 (max)		
			Terminal	35(min)		
			Torque	46 (max)		
Case Style	PRM1-1					

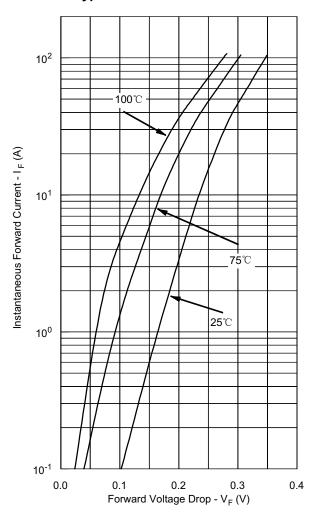
<sup>• 221</sup> West Industry Court E Deer Park, NY 11729-4681 (631) 586-7600 FAX (631) 242-9798 •

<sup>•</sup> World Wide Web Site - http://www.sensitron.com • E-Mail Address - sales@sensitron.com •

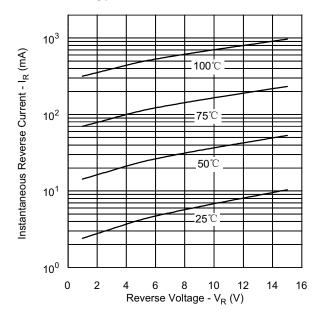
# SENSITRON SEMICONDUCTOR

### Data Sheet 3305, Rev. A

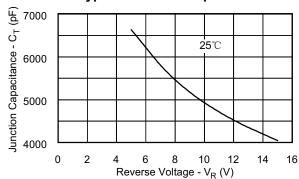
### **Typical Forward Characteristics**



### **Typical Reverse Characteristics**



### **Typical Junction Capacitance**



<sup>•</sup> World Wide Web Site - http://www.sensitron.com • E-Mail Address - sales@sensitron.com •



### Data Sheet 3305, Rev. A

#### **DISCLAIMER:**

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior not ice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
  4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.